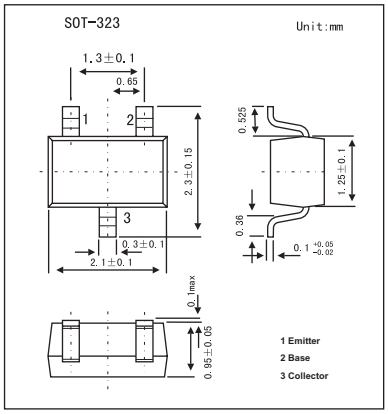
Silicon NPN Epitaxial

2SC4666



■ Features

- High hFE: hFE = 600～3600
- High voltage: VCEO = 50 V
- High collector current: IC = 150 mA (max)
- Small package

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	VCBO	50	V
Collector-emitter voltage	VCEO	50	V
Emitter-base voltage	VEBO	5	V
Collector current	IC	150	mA
Base current	IB	30	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	℃
Storage temperature	Tstg	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	ICBO	VCB = 50 V, IE = 0			0.1	μA
Emitter cut-off current	IEBO	VEB = 5 V, IC = 0			0.1	μA
DC current gain	hFE	VCE = 6 V, IC = 2 mA	600		3600	
Collector-emitter saturation voltage	VCE (sat)	IC = 100 mA, IB = 10 mA		0.12	0.25	V
Transition frequency	fT	VCE = 10 V, IC = 10 mA	100	250		MHz
Collector output capacitance	Cob	VCB = 10 V, IE = 0, f = 1 MHz		3.5		pF
Noise figure	NF(1)	VCE = 6 V, IC = 0.1 mA, f = 100 Hz,Rg = 10 kΩ		0.5		dB
	NF(2)	VCE = 6 V, IC = 0.1 mA, f = 1 kHz,Rg = 10 kΩ		0.3		dB

■ hFE Classification

Marking	P	
Rank	A	B
hFE	600～1800	1200～3600